



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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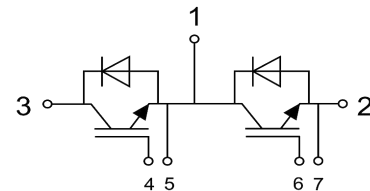
$V_{CES} = 1200V$
 $I_C = 100A$ at $T_C = 80^\circ C$
 $t_{SC} \geq 10\mu sec$
 $V_{CE(ON)} = 1.90V$ at $I_C = 100A$

**IGBT Half-Bridge
 POWIR 62™ Package**



Applications:

- Industrial Motor Drive
- Uninterruptible Power Supply
- Welding and Cutting Machine
- Switched Mode Power Supply
- Induction Heating



Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High Efficiency in a Wide Range of Applications
RBSOA Tested	Rugged Transient Performance
10µsec Short Circuit Safe Operating Area	
POWIR 62™ Package	Industry Standard
Lead Free	RoHS Compliant, Environmental Friendly

Base Part Number	Package Type	Standard Pack	Quantity	Orderable Part Number
IRG7T100HF12B	POWIR 62™	Box	45	IRG7T100HF12B

Absolute Maximum Ratings of IGBT

V_{CES}	Collector to Emitter Voltage	1200	V
V_{GES}	Continuous Gate to Emitter Voltage	±20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C$	100 A
		$T_C = 25^\circ C$	200 A
I_{CM}	Pulse Collector Current	$T_J = 175^\circ C$	200 A
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C, T_J = 175^\circ C$	680 W
T_J	Maximum IGBT Junction Temperature	175	°C
T_{JOP}	Maximum Operating Junction Temperature Range	-40 to +150	°C
T_{stg}	Storage Temperature	-40 to +125	°C

Electrical Characteristics of IGBT at $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$V_{(BR)CES}$	Collector to Emitter Breakdown Voltage	1200			V	$V_{GE} = 0V, I_C = 2mA$	
$V_{GE(th)}$	Gate Threshold Voltage	5.0	5.8	6.5	V	$I_C = 4.8mA, V_{CE} = V_{GE}$	
$V_{CE(ON)}$	Collector to Emitter Saturation Voltage		1.90	2.20	V	$T_J = 25^\circ\text{C}$	$I_C = 100A, V_{GE} = 15V$
			2.20		V	$T_J = 125^\circ\text{C}$	
I_{CES}	Collector to Emitter Leakage Current			2	mA	$V_{GE} = 0V, V_{CE} = V_{CES}$	
I_{GES}	Gate to Emitter Leakage Current			400	nA	$V_{GE} = \pm 20V, V_{CE} = 0$	
R_{Gint}	Internal Gate Resistance		3.40		Ω		

Switching Characteristics of IGBT

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$t_{d(on)}$	Turn-on Delay Time		255		ns	$T_J = 25^\circ\text{C}$	$V_{CC}=600V, I_C = 100A, R_G = 15\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$
			235			$T_J = 125^\circ\text{C}$	
t_r	Rise Time		140		ns	$T_J = 25^\circ\text{C}$	
			140			$T_J = 125^\circ\text{C}$	
$t_{d(off)}$	Turn-off Delay Time		435		ns	$T_J = 25^\circ\text{C}$	
			450			$T_J = 125^\circ\text{C}$	
t_f	Fall Time		170		ns	$T_J = 25^\circ\text{C}$	
			190			$T_J = 125^\circ\text{C}$	
E_{on}	Turn-on Switching Loss		10.1		mJ	$T_J = 25^\circ\text{C}$	
			13.2			$T_J = 125^\circ\text{C}$	
E_{off}	Turn-off Switching Loss		4.90		mJ	$T_J = 25^\circ\text{C}$	
			7.30			$T_J = 125^\circ\text{C}$	
Q_g	Total Gate Charge		850		nC	$T_J = 25^\circ\text{C}$	
C_{ies}	Input Capacitance		13.0		nF	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz, T_J = 25^\circ\text{C}$	
C_{oes}	Output Capacitance		0.76				
C_{res}	Reverse Transfer Capacitance		0.45				
RBSOA	Reverse Bias Safe Operating Area	Trapezoid				$I_C = 200A, V_{CC} = 960V, V_P = 1200V, R_G = 15\Omega, V_{GE} = +15V \text{ to } 0V, T_J = 150^\circ\text{C}$	
SCSOA	Short Circuit Safe Operating Area	10			μs	$V_{CC} = 600V, V_{GE} = 15V, T_J = 150^\circ\text{C}$	

Absolute Maximum Ratings of Freewheeling Diode

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current, $T_C = 25^\circ\text{C}$	200	A
	Diode Continuous Forward Current, $T_C = 80^\circ\text{C}$	100	
I_{FM}	Pulse Diode Current	200	A

Electrical and Switching Characteristics of Freewheeling Diode

Parameter		Typ.	Max.	Unit	Test Conditions	
V_F	Forward Voltage	2.00	2.70	V	$T_J = 25^\circ\text{C}$	$I_F = 100\text{A}$, $V_{GE} = 0\text{V}$
		2.20			$T_J = 125^\circ\text{C}$	
I_{rr}	Peak Reverse Recovery Current	45		A	$T_J = 25^\circ\text{C}$	
		50			$T_J = 125^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	4.9		μC	$T_J = 25^\circ\text{C}$	
		6.0			$T_J = 125^\circ\text{C}$	
E_{rec}	Reverse Recovery Energy	1.7		mJ	$T_J = 25^\circ\text{C}$	
		3.6			$T_J = 125^\circ\text{C}$	

Module Characteristics

Parameter		Min.	Typ.	Max.	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted), $f = 50\text{Hz}$, 1minute			2500	V
$R_{\theta JC}$	Junction-to-Case (IGBT)		0.220		$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (Diode)		0.409		$^\circ\text{C/W}$
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)		0.1		$^\circ\text{C/W}$
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		230		g

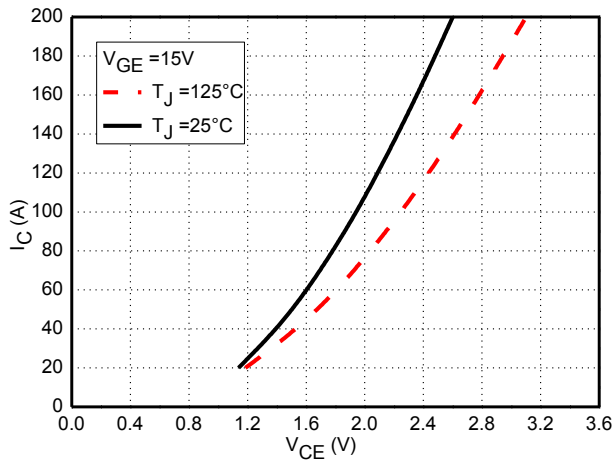


Fig.1 Typical IGBT Saturation Characteristics

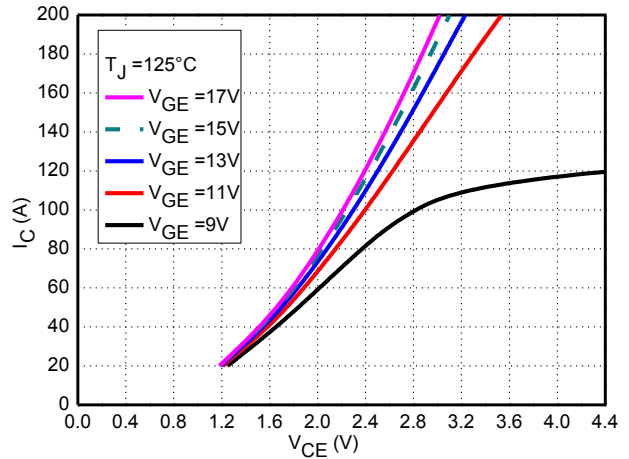


Fig.2 Typical IGBT Output Characteristics

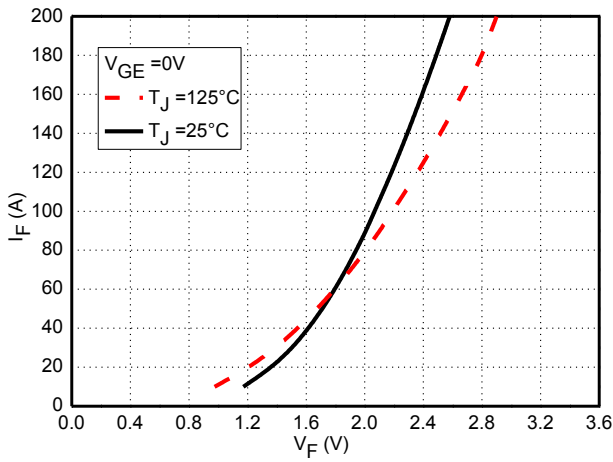


Fig.3 Typical Freewheeling Diode Characteristics

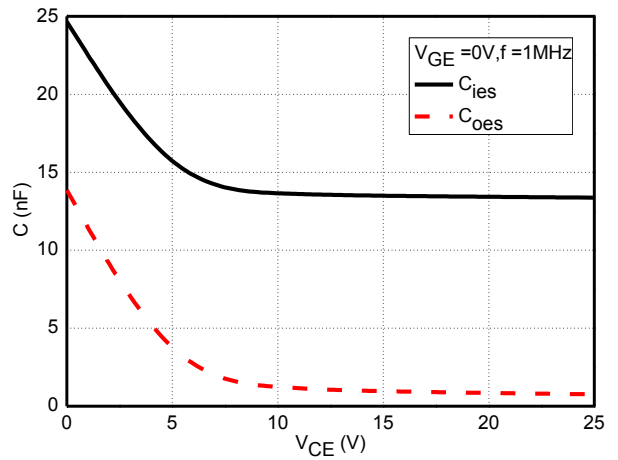


Fig. 4 Typical Capacitance Characteristics

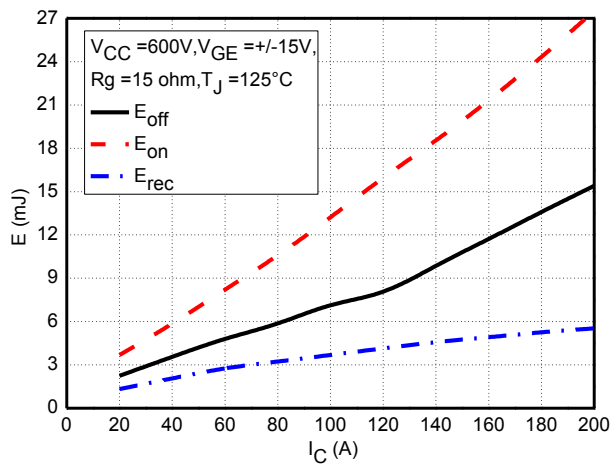


Fig.5 Typical Switching Loss vs. Collector Current

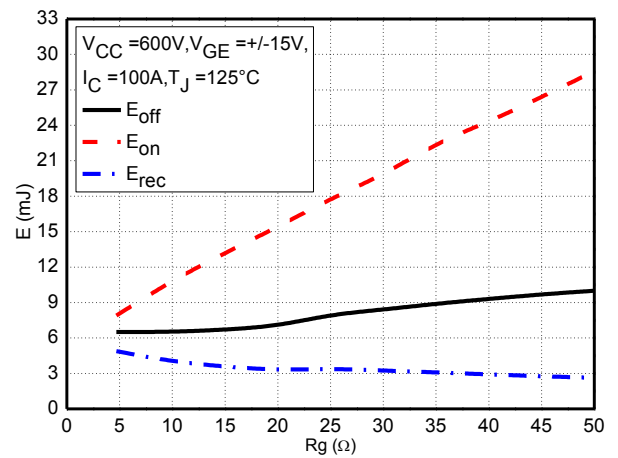


Fig.6 Typical Switching Loss vs. Gate Resistance

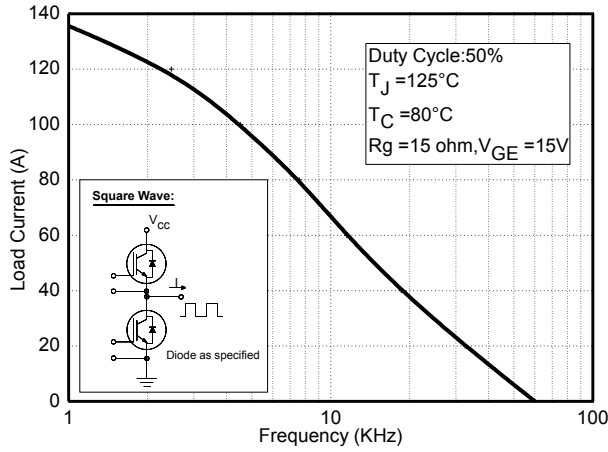


Fig.7 Typical Load Current vs. Frequency

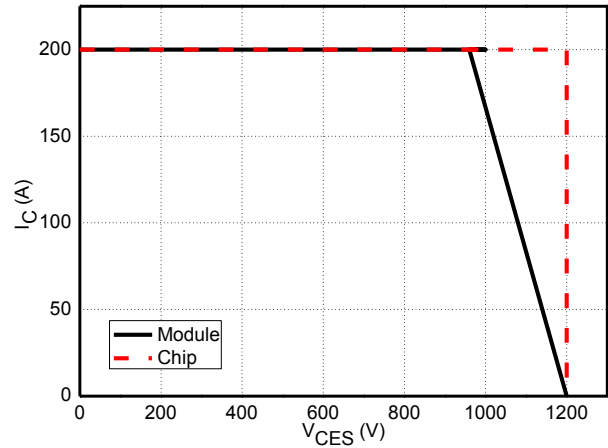


Fig.8 Reverse Bias Safe Operation Area (RBSOA)

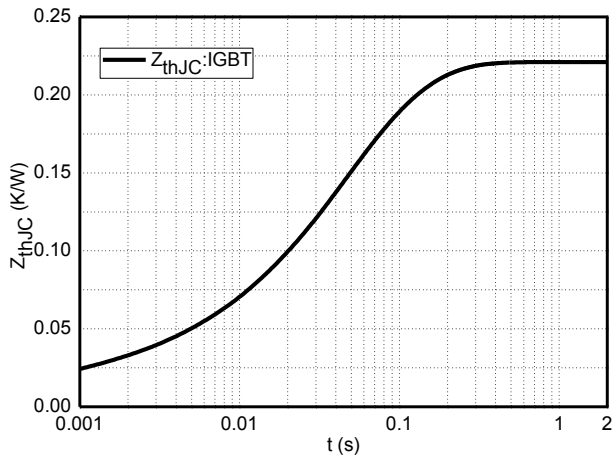


Fig.9 Typical Transient Thermal Impedance (IGBT)

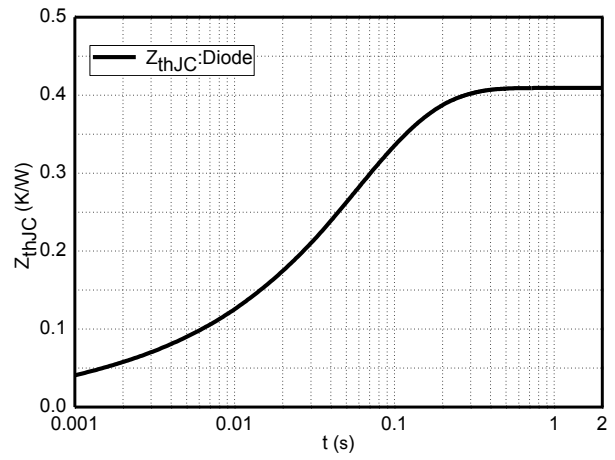


Fig.10 Typical Transient Thermal Impedance (Diode)

